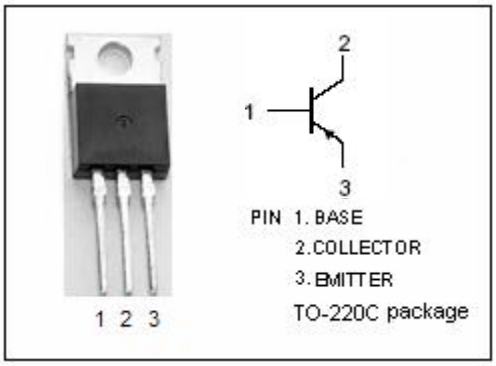
isc Silicon PNP Power Transistor — 2SB630

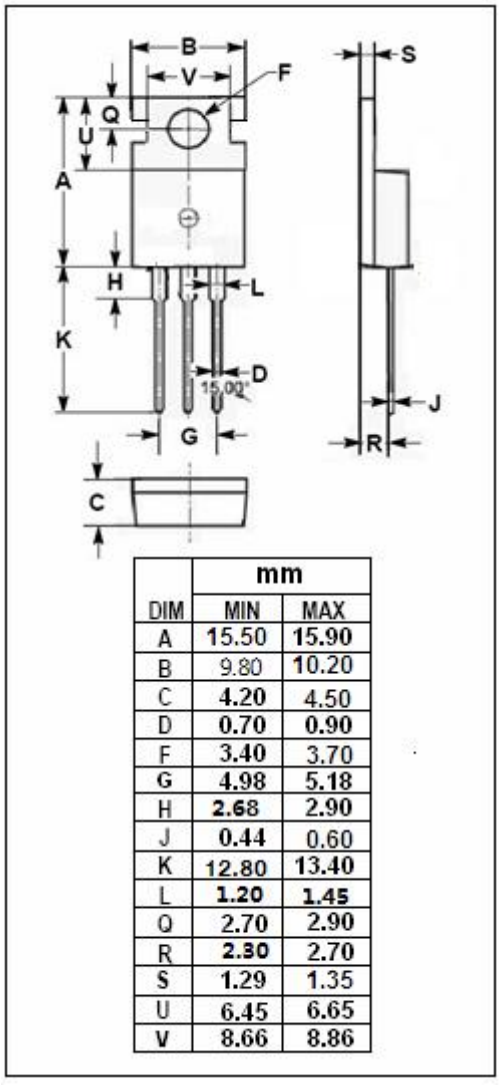


DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -200V(Min)
- Complement to Type 2SD610
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Audio frequency power amplifier applications.
- Suitable for driver of 200~300 watts audio amplifier.



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-200	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-3.0	A
P_C	Collector Power Dissipation @ T_a=25℃	1.5	W
	Collector Power Dissipation @ T_C=25℃	25	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -150V; I_E= 0			-1.0	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -3V; I_C= 0			-1.0	μA
h_{FE-1}	DC Current Gain	I_C= -5mA; V_{CE}= -10V	20			
h_{FE-2}	DC Current Gain	I_C= -0.5A; V_{CE}= -10V	40		200	
C_{OB}	Collector Output Capacitance	I_E= 0; V_{CB}= -10V; f= 1MHz		65		pF
f_T	Current-Gain—Bandwidth Product	I_C= -0.5A; V_{CE}= -10V		4		MHz

◆ **h_{FE-2} Classifications**

S	R	Q
40-80	60-120	100-200